TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

HN1C01FE

Audio Frequency General Purpose Amplifier Applications

- Small package (Dual type)
- High voltage and high current

: $V_{CEO} = 50V$, $I_{C} = 150mA (max)$

High h_{FE} : h_{FE} = 120~400

Excellent hFE linearity

: $h_{FE} (I_C = 0.1 \text{mA}) / h_{FE} (I_C = 2 \text{mA}) = 0.95 \text{ (typ.)}$

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	60	V	
Collector-emitter voltage	V _{CEO}	50	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	Ic	150	mA	
Base current	Ι _Β	30	mA	
Collector power dissipation	P _C *	100	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	

^{*}Total rating

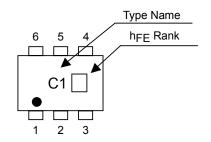
Electrical Characteristics (Ta = 25°C) (Q1,Q2 Common)

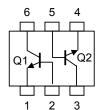
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	V _{CB} = 60V, I _E = 0	_	_	0.1	μΑ
Emitter cut-off current	I _{EBO}	_	V _{EB} = 5V, I _C = 0	_	_	0.1	μΑ
DC current gain	h _{FE (Note)}	_	V _{CE} = 6V, I _C = 2mA	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = 100mA, I _B = 10mA	-	0.1	0.25	٧
Transition frequency	f _T	_	V _{CE} = 10V, I _C = 1mA	80	_	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1MHz	_	2	_	pF

Note:hFE Classification Y (Y): 120~240, GR (G): 200~400 () Marking Symbol

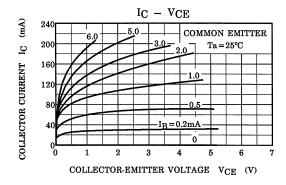
Marking

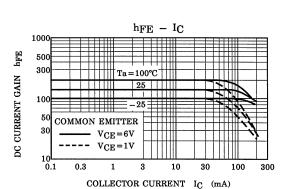
Equivalent Circuit (Top View)

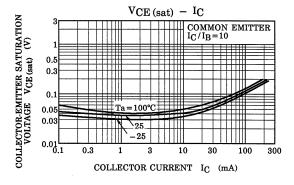


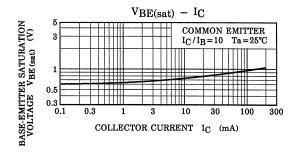


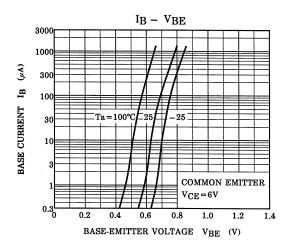
(Q1,Q2 Common)

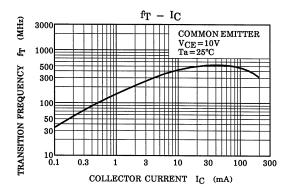


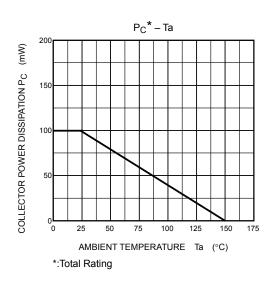












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Handbook" etc..

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